

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +85°C	I <sub>D</sub>	9.8 6.3	A
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	90	A
Avalanche Current (Note 6) (Note 7)			I <sub>AR</sub>	13	A
Repetitive Avalanche Energy (Note 6) (Note 7) L = 0.3mH			E <sub>AR</sub>	25.4	mJ

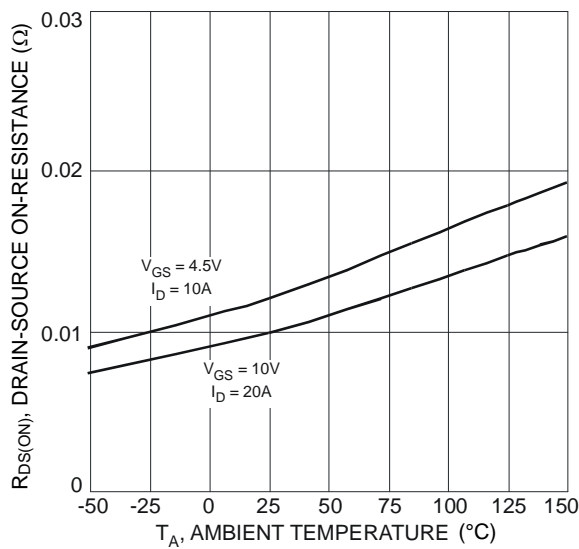
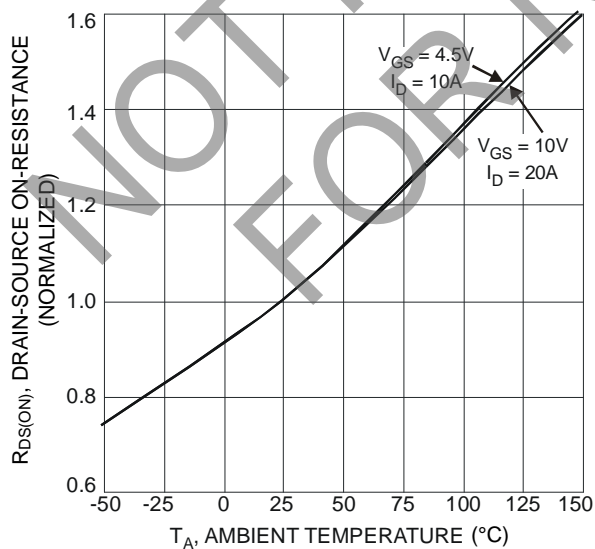
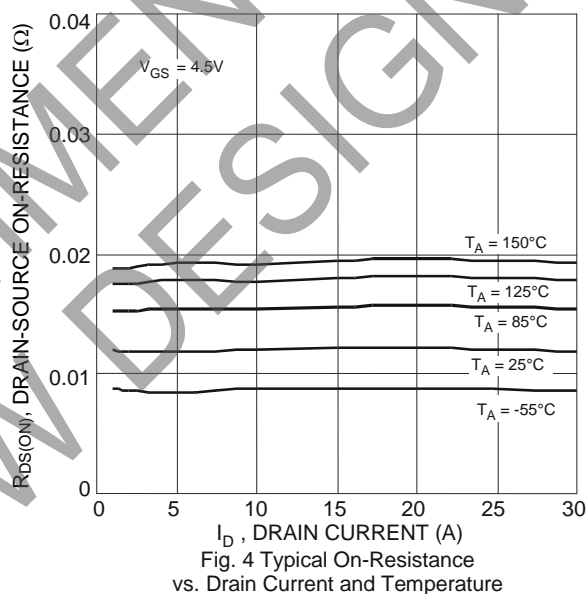
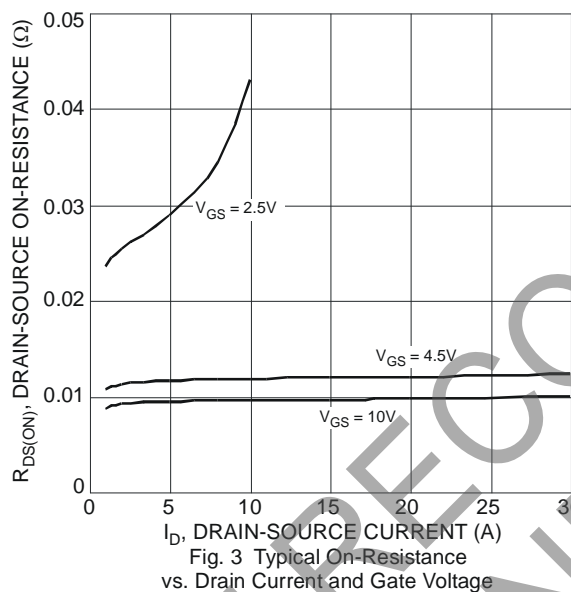
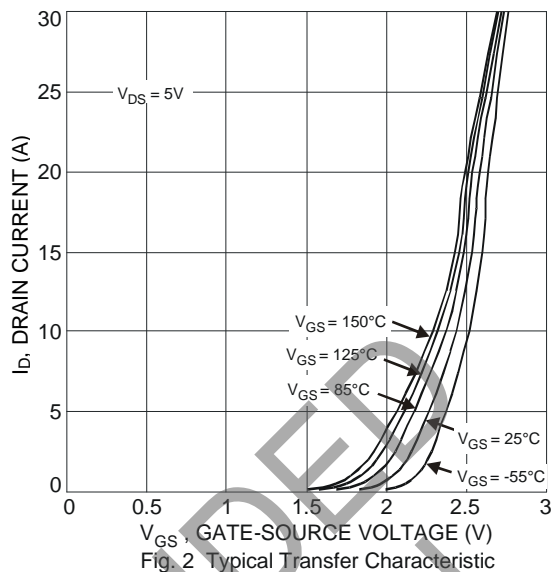
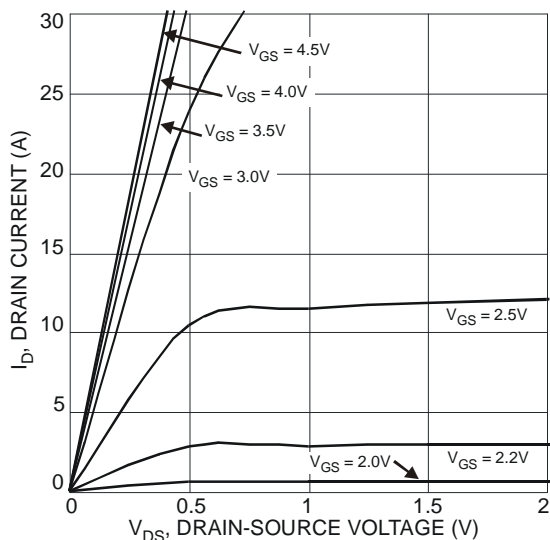
## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	1.54	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	81	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	0.1	mA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	-	2.3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	9	13	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 9.8A
		-	11	16		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 9.8A
		-	-	-		V <sub>DS</sub> = 5V, I <sub>D</sub> = 9.8A
Forward Transfer Admittance	Y <sub>fs</sub>	-	5	-	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 9.8A
Diode Forward Voltage	V <sub>SD</sub>	-	0.4	1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
Maximum Body-Diode + Schottky Continuous Current	I <sub>S</sub>	-	-	5	A	-
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	-	1849	-	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	158	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	123	-	pF	
Gate Resistance	R <sub>g</sub>	0.53	2.68	4.82	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge V <sub>GS</sub> = 4.5V	Q <sub>g</sub>	-	18.5	-	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 9.8A
Total Gate Charge V <sub>GS</sub> = 10V	Q <sub>g</sub>	-	43	-	nC	
Gate-Source Charge	Q <sub>gs</sub>	-	4.7	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>	-	4.0	-	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	-	6.62	-	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 10V, R <sub>g</sub> = 3Ω, R <sub>L</sub> = 1.2Ω
Turn-On Rise Time	t <sub>r</sub>	-	8.73	-	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	36.41	-	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	4.69	-	ns	

- Notes:
5. Device mounted on minimum recommended layout. The value in any given application depends on the user's specific board design.
  6. Repetitive rating, pulse width limited by junction temperature.
  7. I<sub>AR</sub> and E<sub>AR</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to production testing.



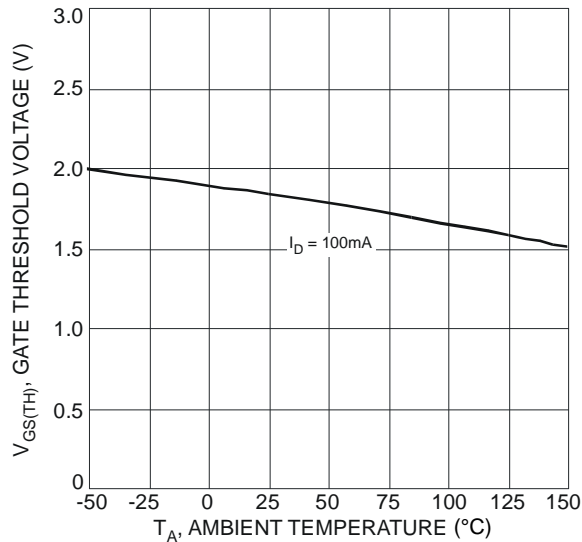


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

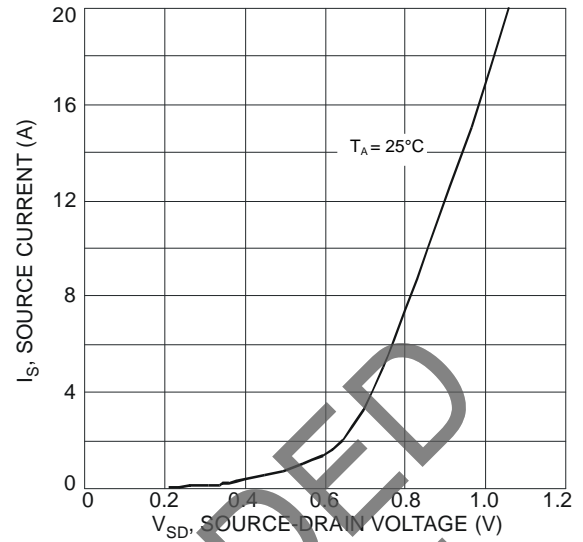


Fig. 8 Diode Forward Voltage vs. Current

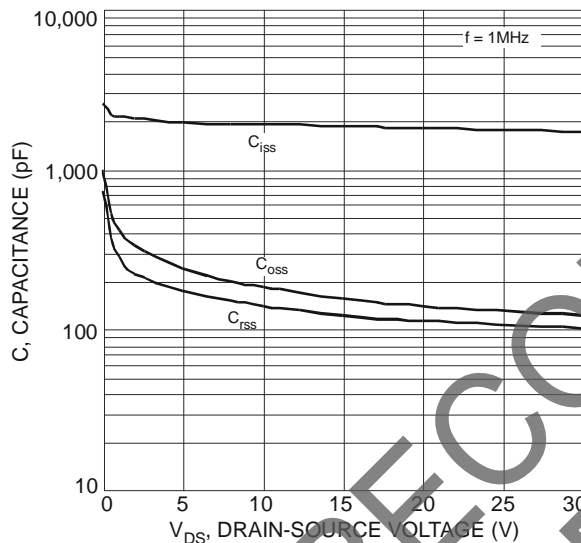


Fig. 9 Typical Total Capacitance

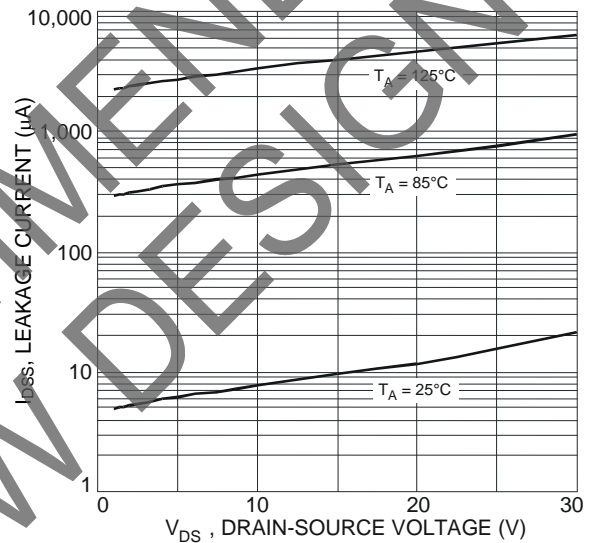


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

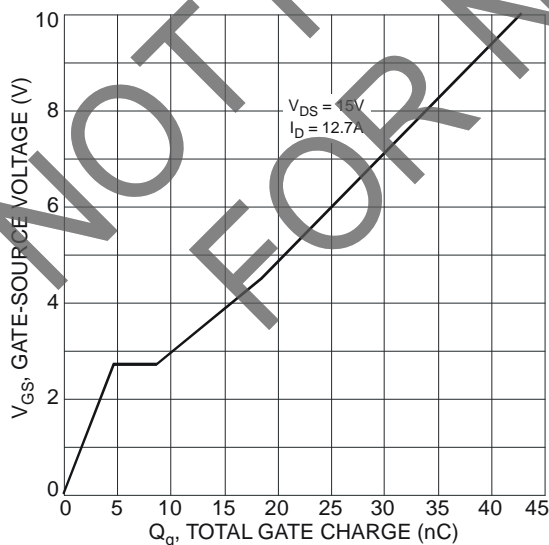


Fig. 11 Gate-Charge Characteristics

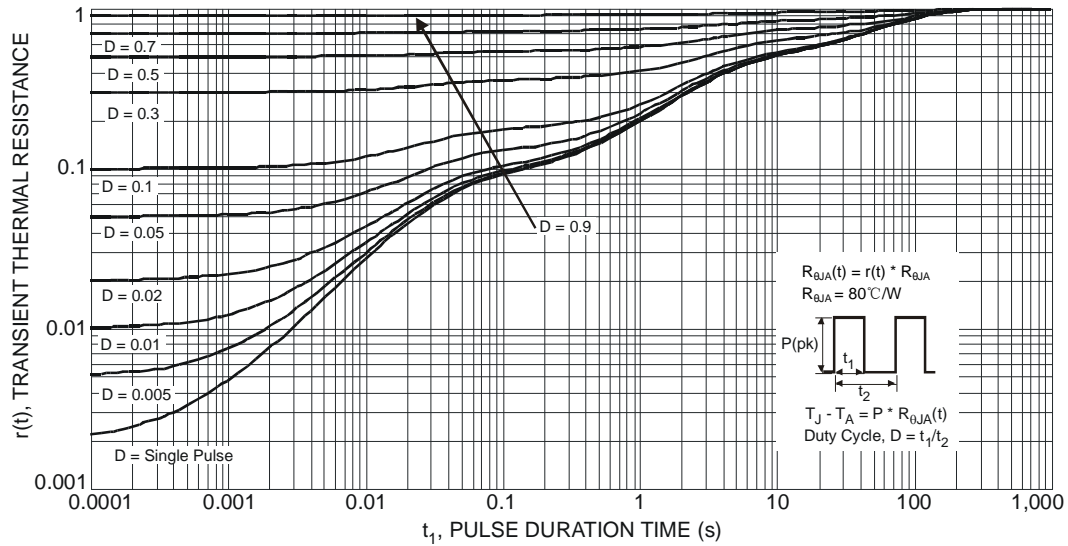
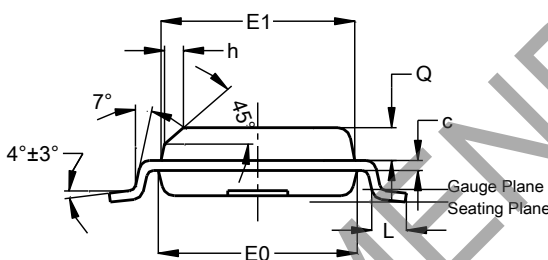
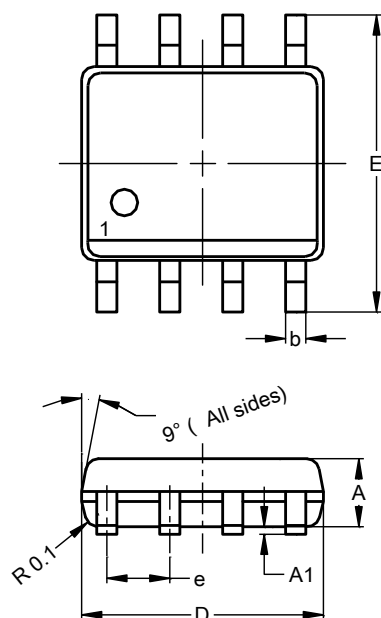


Fig. 12 Transient Thermal Response

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**

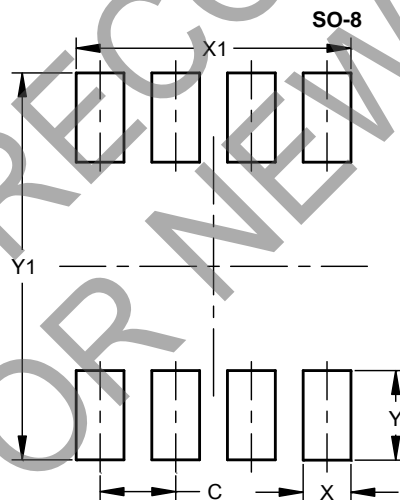


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65

All Dimensions in mm

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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